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Lee

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(54) **THIN FILM RESISTOR**

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CPC ***C22C 19/05*** (2013.01); ***C22C 30/00*** (2013.01); ***H01C 7/006*** (2013.01)

(58) **Field of Classification Search**
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See application file for complete search history.

(56) **References Cited**

PUBLICATIONS

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(57) **ABSTRACT**

A thin film resistor has a higher resistivity compared to that of a conventional thin film resistor. The thin film resistor includes 30-45 at % of nickel, 15-30 at % of chromium, 1-10 at % of manganese, 10-30 at % of yttrium and 1-20 at % of tantalum.

4 Claims, 1 Drawing Sheet